



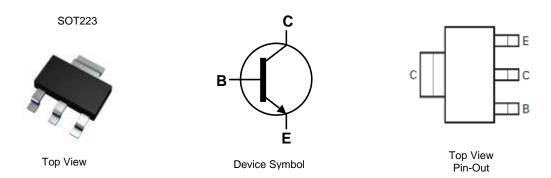
### 25V NPN HIGH CURRENT TRANSISTOR IN SOT223

### **Features**

- BV<sub>CEO</sub> > 25V
- I<sub>C</sub> = 7A High Continuous Collector Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- Very Low Saturation Voltage V<sub>CE(SAT)</sub> < 110mV @ 1A</li>
- R<sub>CE(SAT)</sub> = 36mΩ at 5A for a Low Equivalent On-Resistance
- hFE Specified Up to 20A for a High Gain Hold Up
- P<sub>TOT</sub> = 3W
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
   Solderable per MIL-STD-202, Method 208<sup>3</sup>
- Weight: 0.112 grams (Approximate)



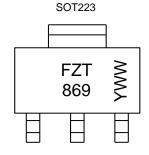
## Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT869TA	AEC-Q101	FZT869	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



FZT 869 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 7 = 2017) WW or  $\overline{W}W$  = Week Code (01–53)



# Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	25	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	I <sub>C</sub>	7	Α
Peak Pulse Current	I <sub>CM</sub>	20	А

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)		3 24	W mW/°C
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.6 12.8	
Thermal Desistance Junction to Ambient	(Note 5)	R <sub>0JA</sub>	42	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	78	°C/W
Thermal Resistance Junction to Lead (Note 7)		$R_{\theta JL}$	8.8	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.

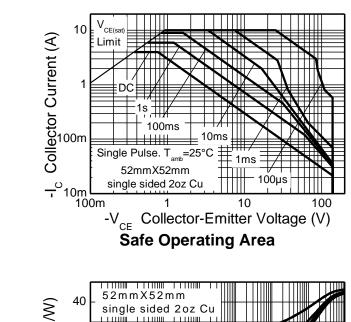
  6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.

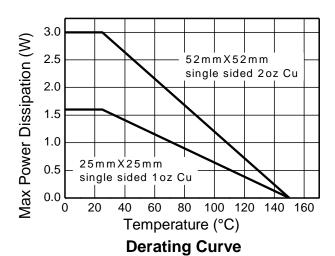
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).

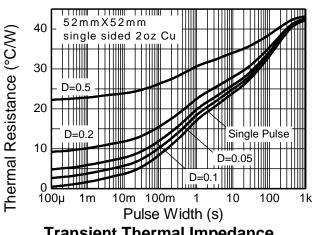
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

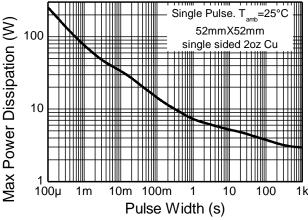


# **Thermal Characteristics and Derating Information**









**Transient Thermal Impedance** 

**Pulse Power Dissipation** 



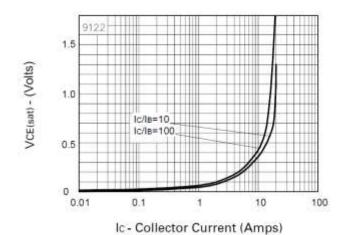
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	60	120	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	60	120	_	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	25	35	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6	8	_	V	$I_{E} = 100 \mu A$
Collector Cut-off Current	I <sub>CBO</sub>	_	_	50 1	nΑ μΑ	V <sub>CB</sub> = 50V V <sub>CB</sub> = 50V, T <sub>A</sub> = +100°C
Collector Cut-off Current	I <sub>CER</sub>	_	_	50 1	nΑ μΑ	$V_{CE} = 50V, R_B \le 1k\Omega$ $V_{CE} = 50V, T_A = +100$ °C
Emitter Cut-off Current	I <sub>EBO</sub>	_	_	10	nA	$V_{EB} = 6V$
		300	450	_	_	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1V
DC Current Coin (Note 0)	L	300	450	_		$I_C = 1A$ , $V_{CE} = 1V$
DC Current Gain (Note 9)	h <sub>FE</sub>	200	300	_		$I_C = 7A$ , $V_{CE} = 1V$
		40	100	_		$I_C = 20A, V_{CE} = 2V$
	V <sub>CE(SAT)</sub>	_	35	50		$I_C = 0.5 \text{mA}, I_B = 10 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		_	67	110	mV	$I_C = 1A, I_B = 10mA$
Collector-Entitler Saturation Voltage (Note 9)		_	168	215	IIIV	$I_C = 2A, I_B = 10mA$
		_	_	350		$I_C = 6.5A$ , $I_B = 150mA$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(SAT)}$	_	_	1.2	V	$I_C = 6.5A$ , $I_B = 300mA$
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(ON)</sub>	_	_	1.13	mV	$I_C = 6.5A, V_{CE} = 1V$
Current Gain-Bandwidth Product (Note 9)	f⊤	_	100	_	MHz	$I_{C} = 100 \text{mA}, V_{CE} = 10 \text{V},$ f = 50 MHz
Output Capacitance	$C_{OBO}$	_	70	_	pF	$V_{CB} = 10V$ , $f = 1MHz$
Switching Times	t <sub>ON</sub>	_	60	_	ns	$I_C = 1A, V_{CC} = 10V,$
Owitering Tillies	toff	_	680	_	115	$I_{B1} = -I_{B2} = 100 \text{mA}$

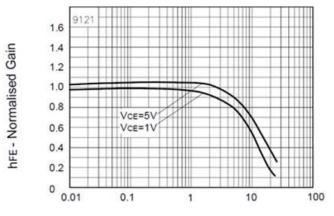
Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

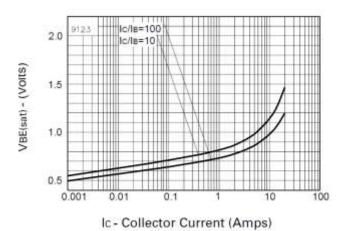


VCE(sat) v IC

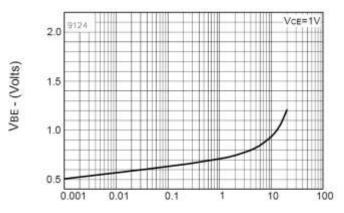


Ic - Collector Current (Amps)

### hFE v IC



VBE(sat) v IC



Ic - Collector Current (Amps)

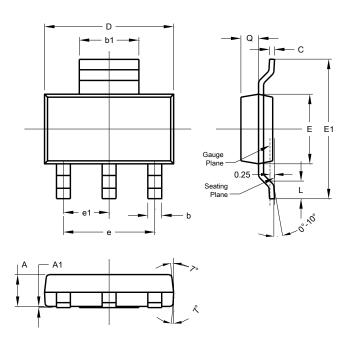
VBE(on) V IC



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT223**

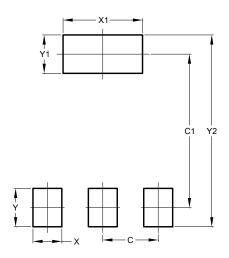


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT223**



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8 00		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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